



SBVS022B - SEPTEMBER 2000 - REVISED JUNE 2009

## 10V Precision Voltage Reference

## **FEATURES**

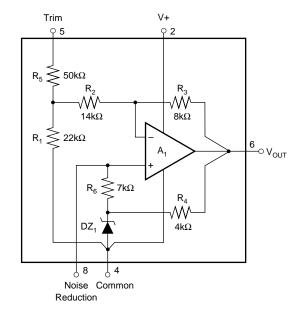
- +10V +0.0025V OUTPUT
- VERY LOW DRIFT: 2.5ppm/°C max
- EXCELLENT STABILITY: 5ppm/1000hr typ
- EXCELLENT LINE REGULATION: 1ppm/V max
- EXCELLENT LOAD REGULATION: 10ppm/mA max
- LOW NOISE: 5μV<sub>PP</sub> typ, 0.1Hz to 10Hz
- WIDE SUPPLY RANGE: 11.4VDC to 36VDC **● LOW QUIESCENT CURRENT: 1.4mA max** PACKAGE OPTIONS: PLASTIC DIP, SO-8

## DESCRIPTION

The REF102 is a precision 10V voltage reference. The drift is laser-trimmed to 2.5ppm/°C max C-grade over the industrial temperature range. The REF102 achieves its precision without a heater. This results in low power, fast warm-up, excellent stability, and low noise. The output voltage is extremely insensitive to both line and load variations and can be externally adjusted with minimal effect on drift and stability. Single-supply operation from 11.4V to 36V and excellent overall specifications make the REF102 an ideal choice for demanding instrumentation and system reference applications.

## **APPLICATIONS**

- PRECISION-CALIBRATED VOLTAGE **STANDARD**
- D/A AND A/D CONVERTER REFERENCE
- PRECISION CURRENT REFERENCE
- ACCURATE COMPARATOR THRESHOLD REFERENCE
- DIGITAL VOLTMETER
- TEST EQUIPMENT
- PC-BASED INSTRUMENTATION





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#### **ABSOLUTE MAXIMUM RATINGS(1)**

Input Voltage+40V
Operating Temperature
P, U –25°C to +85°C
Storage Temperature Range
P, U—40°C to +125°C
Short-Circuit Protection to Common or V+ Continuous

NOTE: (1) Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability.

# ELECTROSTATIC DISCHARGE SENSITIVITY

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

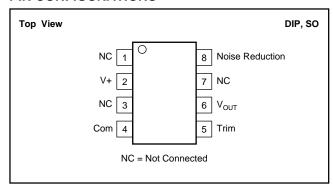
ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

#### PACKAGE/ORDERING INFORMATION(1)

PRODUCT	MAX INITIAL ERROR (mV)	MAX DRIFT (PPM/°C)	PACKAGE-LEAD	PACKAGE DESIGNATOR	PACKAGE MARKING
REF102AU	±10	±10	SO-8	D	REF102AU
REF102AP	±10	±10	DIP-8	P	REF102AP
REF102BU	±5	±5	SO-8	D	REF102BU
REF102BP	±5	±5	DIP-8	P	REF102BP
REF102CU	±2.5	±2.5	SO-8	D	REF102CU
REF102CP	±2.5	±2.5	DIP-8	P	REF102CP

NOTE: (1) For the most current package and ordering information, see the Package Option Addendum at the end of this data sheet, or see the TI website at www.ti.com.

#### **PIN CONFIGURATIONS**



## **ELECTRICAL CHARACTERISTICS**

At  $T_A$  = +25°C and  $V_S$  = +15V power supply, unless otherwise noted.

			REF102A			REF102B					
PARAMETER	CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	UNITS
OUTPUT VOLTAGE											
Initial	$T_A = 25^{\circ}C$	9.99		10.01	9.995		10.005	9.9975		10.0025	V
vs Temperature (1)				10			5			2.5	ppm/°C
vs Supply											
(Line Regulation)	$V_S = 11.4V \text{ to } 36V$			2			1			1	ppm/V
vs Output Current											
(Load Regulation)	$I_L = 0mA \text{ to } +10mA$			20			10			10	ppm/mA
	$I_L = 0mA \text{ to } -5mA$			40			20			20	ppm/mA
vs Time	$T_A = +25^{\circ}C$										
M Package			5			*			*		ppm/1000hr
P, U Packages (2)			20			*					ppm/1000hr
Trim Range (3)		±3			*			*			%
Capacitive Load, max			1000			*			*		pF
NOISE	0.1Hz to 10Hz		5			*			*		$\mu V_{PP}$
OUTPUT CURRENT		+10, –5			*			*			mA
INPUT VOLTAGE											
RANGE		+11.4		+36	*		*	*		*	V
QUIESCENT CURRENT	I <sub>OUT</sub> = 0			+1.4			*			*	mA
WARM-UP TIME (4)	To 0.1%		15			*			*		μs
TEMPERATURE											
RANGE											
Specification											
REF102A, B, C		-25		+85	*		*	*		*	°C

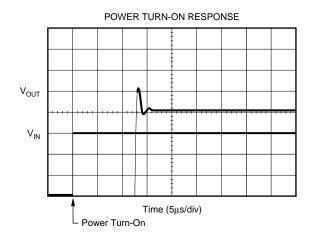
<sup>\*</sup> Specifications same as REF102A.

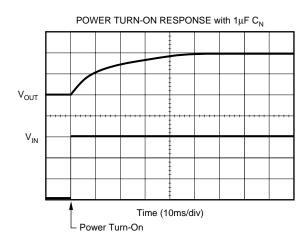
NOTES: (1) The box method is used to specify output voltage drift vs temperature; see the Discussion of Performance section.

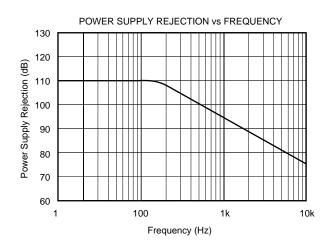
- (2) Typically 5ppm/1000hrs after 168hr powered stabilization.
- (3) Trimming the offset voltage affects drift slightly. See Installation and Operating Instructions for details.
- (4) With noise reduction pin floating. See Typical Characteristics for details.

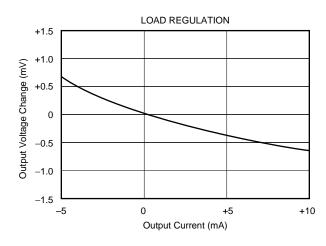
## **TYPICAL CHARACTERISTICS**

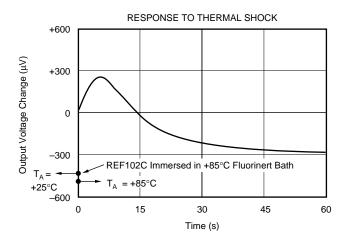
At  $T_A = +25^{\circ}C$ ,  $V_S = +15V$ , unless otherwise noted.

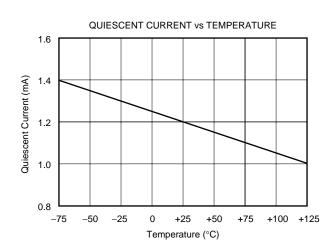






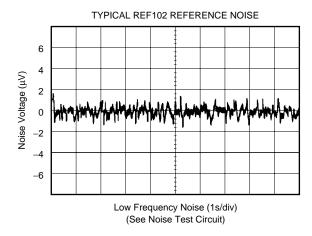


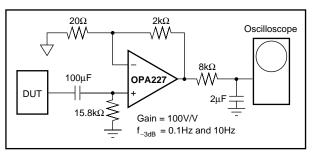




## **TYPICAL CHARACTERISTICS (Cont.)**

At  $T_A = +25^{\circ}C$ ,  $V_S = +15V$ , unless otherwise noted.





Noise Test Circuit.

### THEORY OF OPERATION

Refer to the diagram on the first page of this data sheet. The 10V output is derived from a compensated buried zener diode  $DZ_1$ , op amp  $A_1$ , and resistor network  $R_1 - R_6$ .

Approximately 8.2V is applied to the non-inverting input of  $A_1$  by  $DZ_1,\,R_1,\,R_2,\,$  and  $R_3$  are laser-trimmed to produce an exact 10V output. The zener bias current is established from the regulated output voltage through  $R_4,\,R_5$  allows user-trimming of the output voltage by providing for small external adjustment of the amplifier gain. Because the temperature coefficient (TCR) of of  $R_5$  closely matches the TCR of  $R_1,\,R_2$  and  $R_3$ , the voltage trim has minimal effect on the reference drift. The output voltage noise of the REF102 is dominated by the noise of the zener diode. A capacitor can be connected between the Noise Reduction pin and ground to form a low-pass filter with  $R_6$  and roll off the high-frequency noise of the zener.

## DISCUSSION OF PERFORMANCE

The REF102 is designed for applications requiring a precision voltage reference where both the initial value at room temperature and the drift over temperature are of importance to the user. Two basic methods of specifying voltage reference drift versus temperature are in common usage in the industry—the butterfly method and the box method. The

REF102 is specified by the more commonly-used *box method*. The *box* is formed by the high and low specification temperatures and a diagonal, the slope of which is equal to the maximum specified drift.

Since the shape of the actual drift curve is not known, the vertical position of the box is not known, either. It is, however, bounded by  $V_{UPPER\ BOUND}$  and  $V_{LOWER\ BOUND}$  (see Figure 1). Figure 1 uses the REF102CU as an example. It has a drift specification of 2.5ppm/°C maximum and a specification temperature range of  $-25^{\circ}$ C to  $+85^{\circ}$ C. The box height,  $V_1$  to  $V_2$ , is 2.75mV.

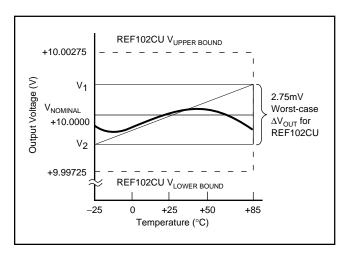


FIGURE 1. REF102CU Output Voltage Drift.

## INSTALLATION AND OPERATING INSTRUCTIONS

#### **BASIC CIRCUIT CONNECTION**

Figure 2 shows the proper connection of the REF102. To achieve the specified performance, pay careful attention to layout. A low resistance star configuration will reduce voltage errors, noise pickup, and noise coupled from the power supply. Commons should be connected as indicated, being sure to minimize interconnection resistances.

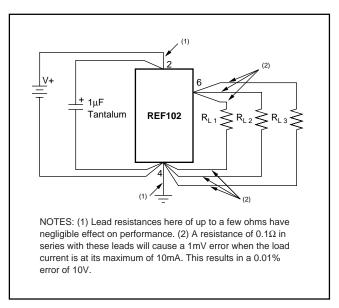


FIGURE 2. REF102 Installation.

#### **OPTIONAL OUTPUT VOLTAGE ADJUSTMENT**

Optional output voltage adjustment circuits are shown in Figures 3 and 4. Trimming the output voltage will change the voltage drift by approximately 0.008ppm/°C per mV of trimmed voltage. In the circuit in Figure 3, any mismatch in TCR between the two sections of the potentiometer will also affect drift, but the effect of the  $\Delta$ TCR is reduced by a factor of five by the internal resistor divider. A high quality potentiometer, with good mechanical stability, such as a cermet, should be

used. The circuit in Figure 3 has a minimum trim range of  $\pm 300$ mV. The circuit in Figure 4 has less range but provides higher resolution. The mismatch in TCR between R<sub>S</sub> and the internal resistors can introduce some slight drift. This effect is minimized if R<sub>S</sub> is kept significantly larger than the 50k $\Omega$  internal resistor. A TCR of 100ppm/°C is normally sufficient.

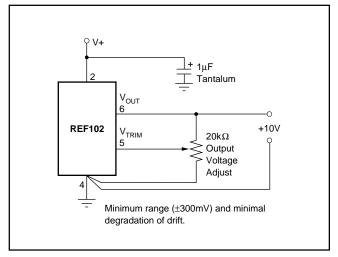


FIGURE 3. REF102 Optional Output Voltage Adjust.

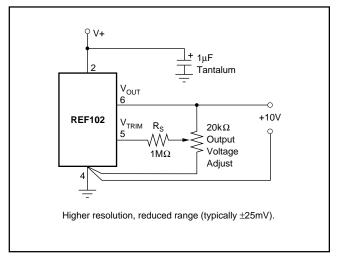


FIGURE 4. REF102 Optional Output Voltage, Fine Adjust.

#### **OPTIONAL NOISE REDUCTION**

The high-frequency noise of the REF102 is dominated by the zener diode noise. This noise can be greatly reduced by connecting a capacitor between the Noise Reduction pin and ground. The capacitor forms a low-pass filter with  $R_6$  (refer to the figure on page 1) and attenuates the high-frequency noise generated by the zener. Figure 5 shows the effect of a  $1\mu F$  noise reduction capacitor on the high-frequency noise of the REF102.  $R_6$  is typically  $7k\Omega$  so the filter has a -3dB frequency of about 22Hz. The result is a reduction in noise from about  $800\mu V_{PP}$  to under  $200\mu V_{PP}$ . If further noise reduction is required, use the circuit in Figure 14.

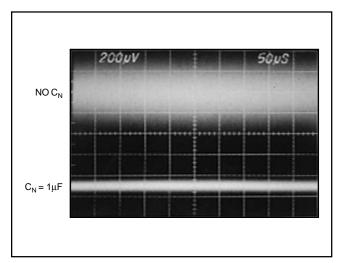


FIGURE 5. Effect of  $1\mu F$  Noise Reduction Capacitor on Broadband Noise (f\_3dB = 1MHz)

## **APPLICATIONS INFORMATION**

High accuracy, extremely low drift, outstanding stability, and low cost make the REF102 an ideal choice for all instrumentation and system reference applications. Figures 6 through 14 show a variety of useful application circuits.

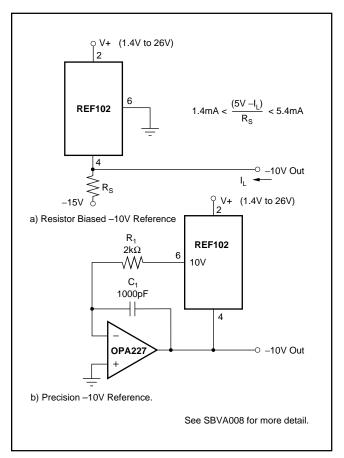


FIGURE 6. -10V Reference Using a) Resistor or b) OPA227.

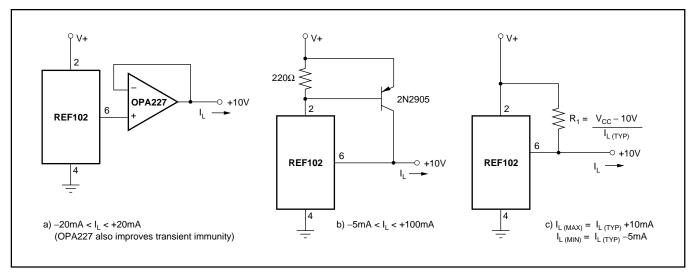


FIGURE 7. +10V Reference With Output Current Boosted to: a)  $\pm$ 20mA, b) +100mA, and c)  $I_{L (TYP)}$  +10mA, -5A.

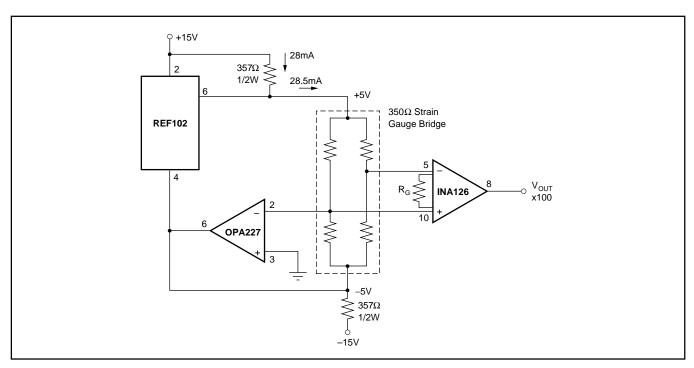


FIGURE 8. Strain Gauge Conditioner for  $350\Omega$  Bridge.

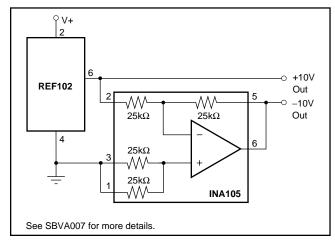


FIGURE 9. ±10V Reference.

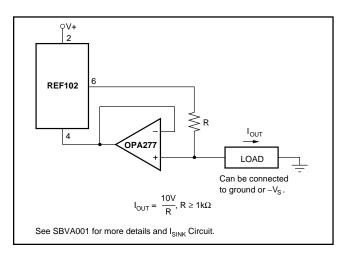
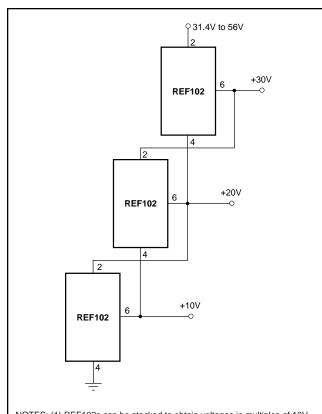


FIGURE 10. Positive Precision Current Source.





NOTES: (1) REF102s can be stacked to obtain voltages in multiples of 10V. (2) The supply voltage should be between 10n + 1.4 and 10n + 26, where *n* is the number of REF102s. (3) Output current of each REF102 must not exceed its rated output current of +10, -5mA. This includes the current delivered to the lower REF102.

FIGURE 11. Stacked References.

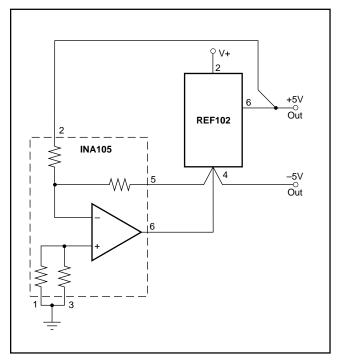


FIGURE 12. ±5V Reference.

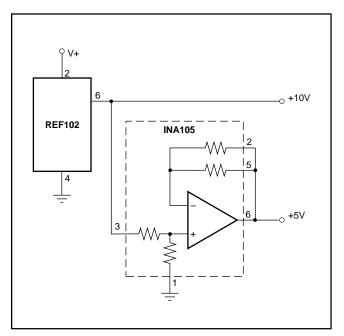


FIGURE 13. +5V and +10V Reference.

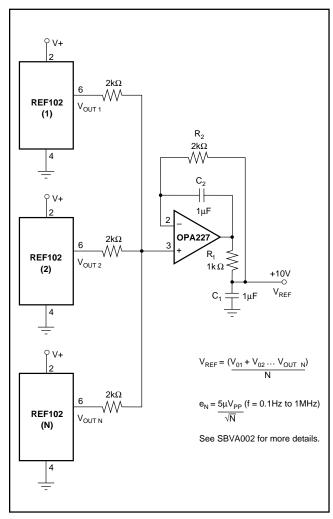


FIGURE 14. Precision Voltage Reference with Extremely Low Noise.

## **Revision History**

DATE	REVISION	PAGE	SECTION	DESCRIPTION
6/09	D	2	Absolute Maximum Ratings	Deleted lead temperature rating.
6/09	Б	2	Package/Ordering Information	Changed Package Ordering Information table.

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.







24-Aug-2018

#### **PACKAGING INFORMATION**

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
REF102AP	ACTIVE	PDIP	Р	8	50	Green (RoHS & no Sb/Br)	CU NIPDAU	N / A for Pkg Type		REF102P A	Samples
REF102AU	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR		REF 102U A	Samples
REF102AU/2K5	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR		REF 102U A	Samples
REF102AUG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR		REF 102U A	Samples
REF102BP	ACTIVE	PDIP	Р	8	50	Green (RoHS & no Sb/Br)	CU NIPDAU	N / A for Pkg Type		REF102P B	Samples
REF102BU	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-25 to 85	REF 102U B	Samples
REF102BUG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-25 to 85	REF 102U B	Samples
REF102CP	ACTIVE	PDIP	Р	8	50	Green (RoHS & no Sb/Br)	CU NIPDAU	N / A for Pkg Type	-25 to 85	REF102P C	Samples
REF102CPG4	ACTIVE	PDIP	Р	8	50	Green (RoHS & no Sb/Br)	CU NIPDAU	N / A for Pkg Type	-25 to 85	REF102P C	Samples
REF102CU	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-25 to 85	REF 102U C	Samples
REF102CU/2K5	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-25 to 85	REF 102U C	Samples
REF102CUG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-25 to 85	REF 102U C	Samples

<sup>(1)</sup> The marketing status values are defined as follows: **ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.



#### PACKAGE OPTION ADDENDUM

24-Aug-2018

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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## **PACKAGE MATERIALS INFORMATION**

www.ti.com 26-Jan-2013

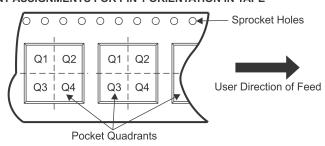
### TAPE AND REEL INFORMATION





Α0	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

1	7 iii dimononono dio monima				000					1/0	B4	144	D: 4
	Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
	REF102AU/2K5	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
	REF102CU/2K5	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

www.ti.com 26-Jan-2013



#### \*All dimensions are nominal

Device	Package Type Package Drawing		Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
REF102AU/2K5	SOIC	D	8	2500	367.0	367.0	35.0
REF102CU/2K5	SOIC	D	8	2500	367.0	367.0	35.0

## D (R-PDSO-G8)

### PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AA.





SMALL OUTLINE INTEGRATED CIRCUIT



#### NOTES:

- 1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.
- 5. Reference JEDEC registration MS-012, variation AA.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE INTEGRATED CIRCUIT



#### NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



## P (R-PDIP-T8)

## PLASTIC DUAL-IN-LINE PACKAGE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-001 variation BA.



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